

DSA10I100PM

preliminary

 $V_{RRM} = 100 V$

 $I_{FAV} = 10 A$

 $V_F = 0.71 V$

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Schottky Diode Gen²

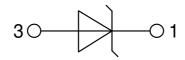
Part number

DSA10I100PM



Backside: isolated





Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

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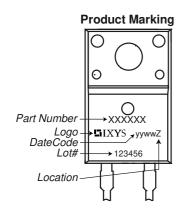
Schottky					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			100	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			100	٧
IR	reverse current, drain current	$V_R = 100 \text{ V}$	$T_{VJ} = 25^{\circ}C$			200	μΑ
		$V_R = 100 V$	$T_{VJ} = 125$ °C			2	mΑ
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			0.89	V
		$I_F = 20 A$				1.04	٧
		I _F = 10 A	T _{vJ} = 125°C			0.71	٧
		$I_F = 20 A$				0.87	٧
I _{FAV}	average forward current	T _C = 140°C	T _{vJ} = 175°C			10	Α
		rectangular $d = 0.5$					i
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.45	٧
\mathbf{r}_{F}	slope resistance } for power lo	oss calculation only				16.1	mΩ
R _{thJC}	thermal resistance junction to cas	e				4.5	K/W
R _{thCH}	thermal resistance case to heatsing	nk			0.5		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			35	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			240	Α
C¹	junction capacitance	$V_R = 12 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		96		pF



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Package TO-220FP				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					35	Α
T _{VJ}	virtual junction temperature				-55		175	°C
Top	operation temperature				-55		150	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	N
$d_{\text{Spp/App}}$	creenage distance on surface	Letriking dietance through air	terminal to terminal	3.2	2.7			mm
$d_{Spb/Apb}$	creepage distance on surface striking distance th		terminal to backside	2.5	2.5			mm
V _{ISOL}	isolation voltage	t = 1 second	50/00 II		2500			V
	$t = 1 \text{ minute}$ 50/60 Hz, RMS; $l_{ISOL} \le 1 \text{ mA}$			2100			٧	



Part description

D = Diode S = Schottky Diode

A = low VF 10 = Current Rating [A]

I = Single Diode 100 = Reverse Voltage [V] PM = TO-220ACFP (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA10I100PM	DSA10I100PM	Tube	50	503362

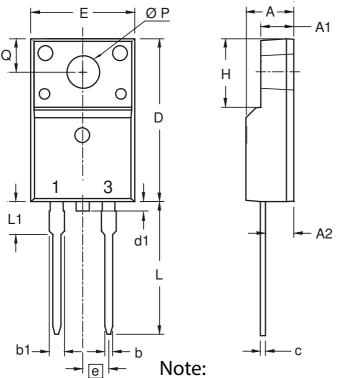
Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$)—[R_o]-	Schottky		
V _{0 max}	threshold voltage	0.45		V
$R_{0 max}$	slope resistance *	12.9		$m\Omega$





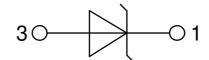
preliminary

Outlines TO-220FP



 C
Note:
All metal surface are
matte pure tin plated
except trimmed area.

Dim.	Millim	Millimeters		hes	
DIIII.	min	max	min	max	
Α	4.50	4.90	0.177	0.193	
A1	2.34	2.74	0.092	0.108	
A2	2.56	2.96	0.101	0.117	
b	0.70	0.90	0.028	0.035	
b1	1.27	1.47	0.050	0.058	
С	0.45	0.60	0.018	0.024	
D	15.67	16.07	0.617	0.633	
d1	0	1.10	0	0.043	
Е	9.96	10.36	0.392	0.408	
е	2.54	BSC	0.100	BSC	
Н	6.48	6.88	0.255	0.271	
L	12.68	13.28	0.499	0.523	
L1	3.03	3.43	0.119	0.135	
ØΡ	3.08	3.28	0.121	0.129	
Q	3.20	3.40	0.126	0.134	





Schottky

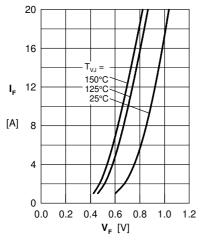


Fig. 1 Maximum forward voltage drop characteristics

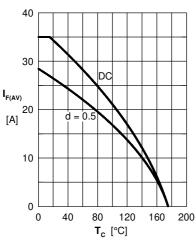


Fig. 4 Avg: forward current $I_{F(AV)}$ vs. case temperature T_C

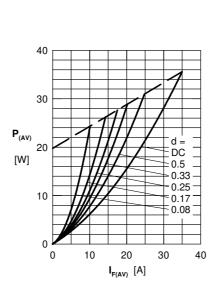


Fig. 5 Forward power loss characteristics

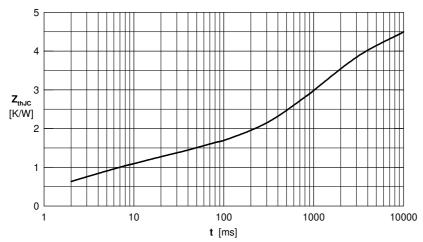


Fig. 6 Transient thermal impedance junction to case

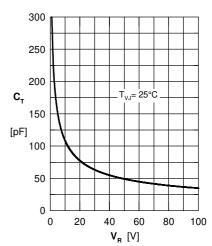


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

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